Diode Semiconductor Device - Page 1 of 1



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| | re Material: |
|-----------|--|
| Metal | Learnet lea |
| Overall | - |
| | 0.234 inches and 0.246 inches |
| | Il Length: |
| 0.990 ind | |
| | Diameter: |
| | 0.395 inches and 0.405 inches |
| | ng Method: |
| Termina | |
| | s Provided: |
| | cally sealed case |
| Semico | nductor Material: |
| Silicon | |
| Voltage | Rating In Volts Per Characteristic: |
| 600.0 re | everse voltage, peak |
| Current | Rating Per Characteristic: |
| 22.00 an | nperes forward current, average |
| Maximu | m Operating Tempurature Per Measurement Point: |
| 175.0 de | grees celsius junction |
| Termina | Il Type And Quantity: |
| 2 uninsu | lated wire lead |
| Shelf Lit | fe: |
| N/a | |
| Unit Of | Measure: |
| | |
| Demilita | rization: |
| No | |
| Fiig: | |
| A110a0 | |